

## P-Channel 15 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 15	27 at V <sub>GS</sub> = - 4.5 V	- 8	12.5 nC
	38 at V <sub>GS</sub> = - 2.5 V		

### FEATURES

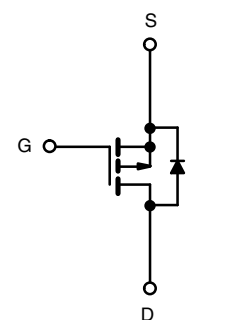
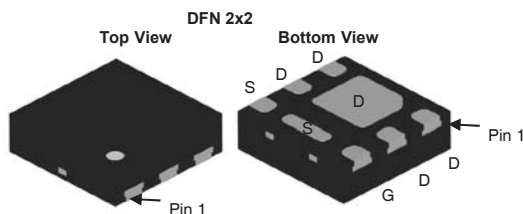
- DT-Trench Power MOSFET
- 100 % R<sub>G</sub> and UIS Tested
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge



**RoHS**  
COMPLIANT

### APPLICATIONS

- PWM Applications
- Load Switch
- Battery charge in cellular handset



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	- 15	V
Gate-Source Voltage	V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 8
		T <sub>C</sub> = 100 °C	- 4.6
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 32	A
Maximum Power Dissipation <sup>c</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	2.6
		T <sub>C</sub> = 100 °C	1.04
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	78	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	48	

### Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.
- The value of R<sub>thJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.

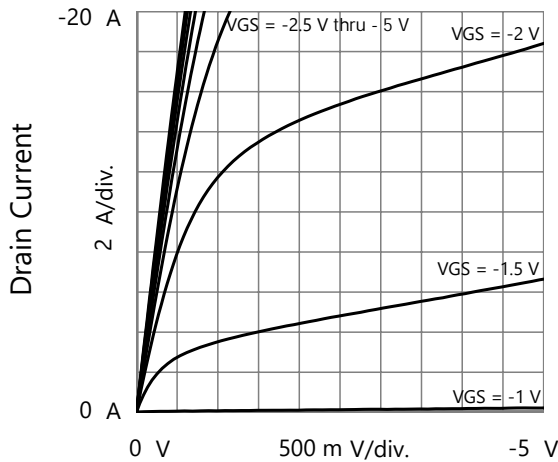
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0, I_D = -250\text{ }\mu\text{A}$	-15			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-50	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	-8			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$		27	33	m $\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -4\text{ A}$		38	49	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -7\text{ A}$		20		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		610		pF
Output Capacitance	$C_{oss}$			117		
Reverse Transfer Capacitance	$C_{rss}$			100		
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4\text{ A}$		12.5		nC
Gate-Source Charge	$Q_{gs}$			1.5		
Gate-Drain Charge	$Q_{gd}$			3		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		50		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -2.5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 3\text{ }\Omega$		12		ns
Rise Time	$t_r$			10		
Turn-Off Delay Time	$t_{d(off)}$			19		
Fall Time	$t_f$			25		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-8	A
Pulse Diode Forward Current	$I_{SM}$				-32	
Body Diode Voltage	$V_{SD}$	$I_S = -1\text{ A}$			-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$				4	

**Notes:**

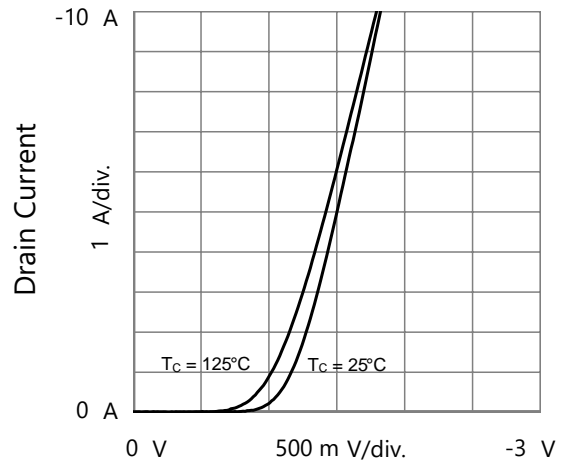
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

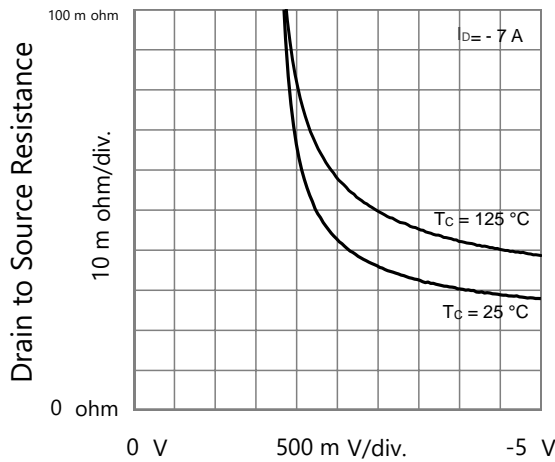
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



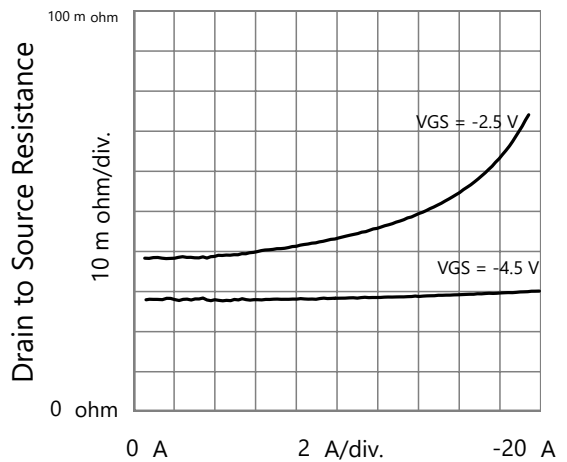
Drain to Source Voltage  
Output Characteristics



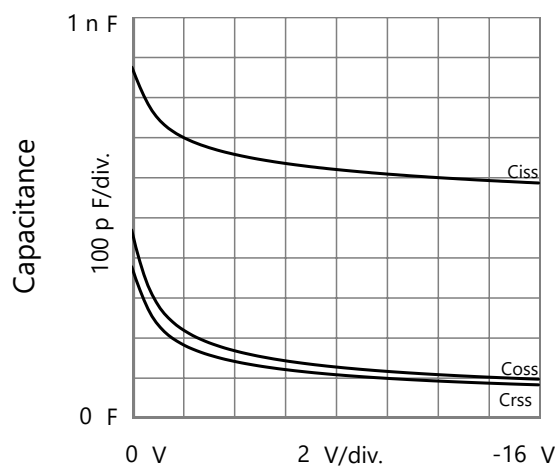
Gate to Source Voltage  
Transfer Characteristics



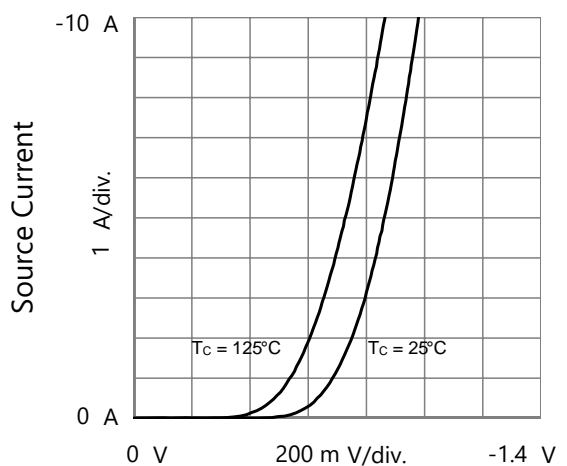
Gate to Source Voltage  
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current  
Drain to Source Resistance vs. Drain Current

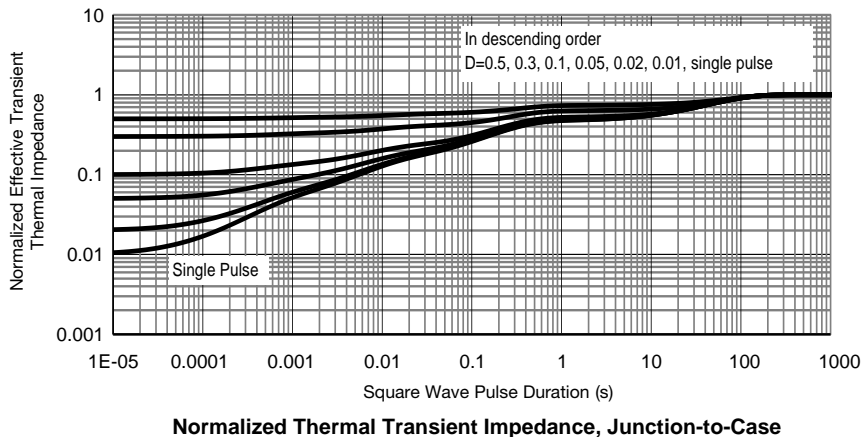
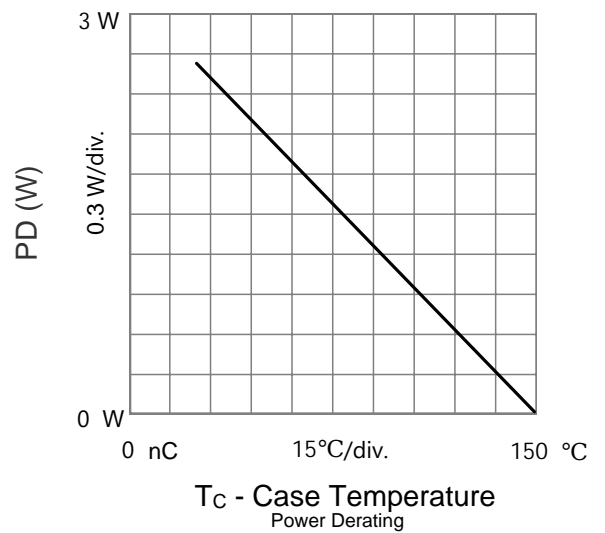
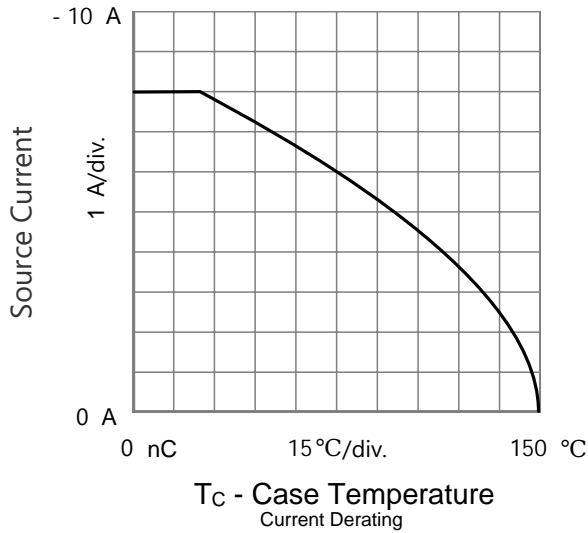
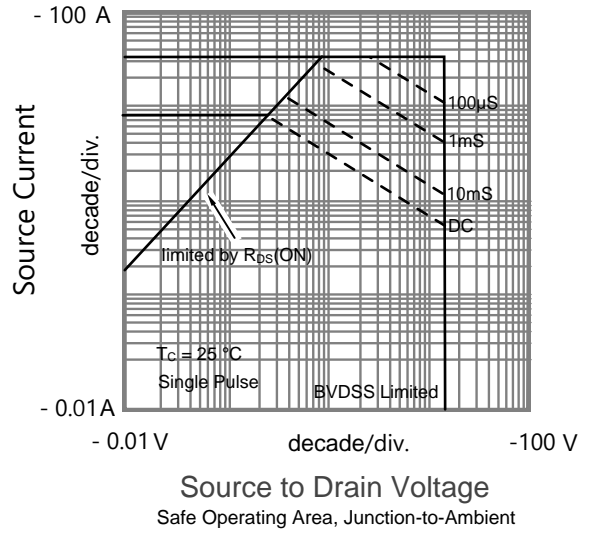
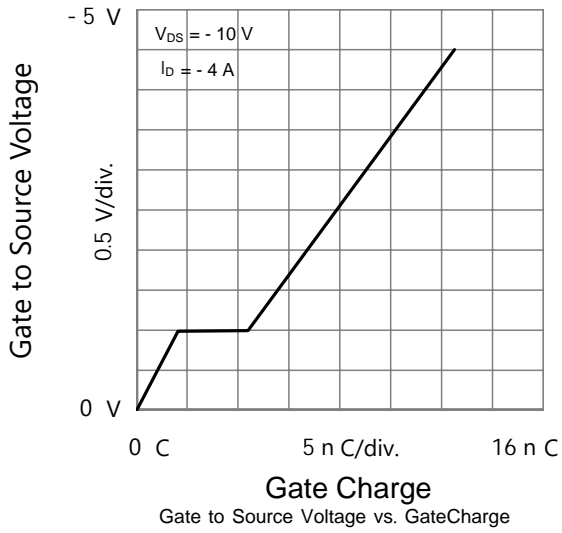


Drain to Source Voltage  
Capacitances

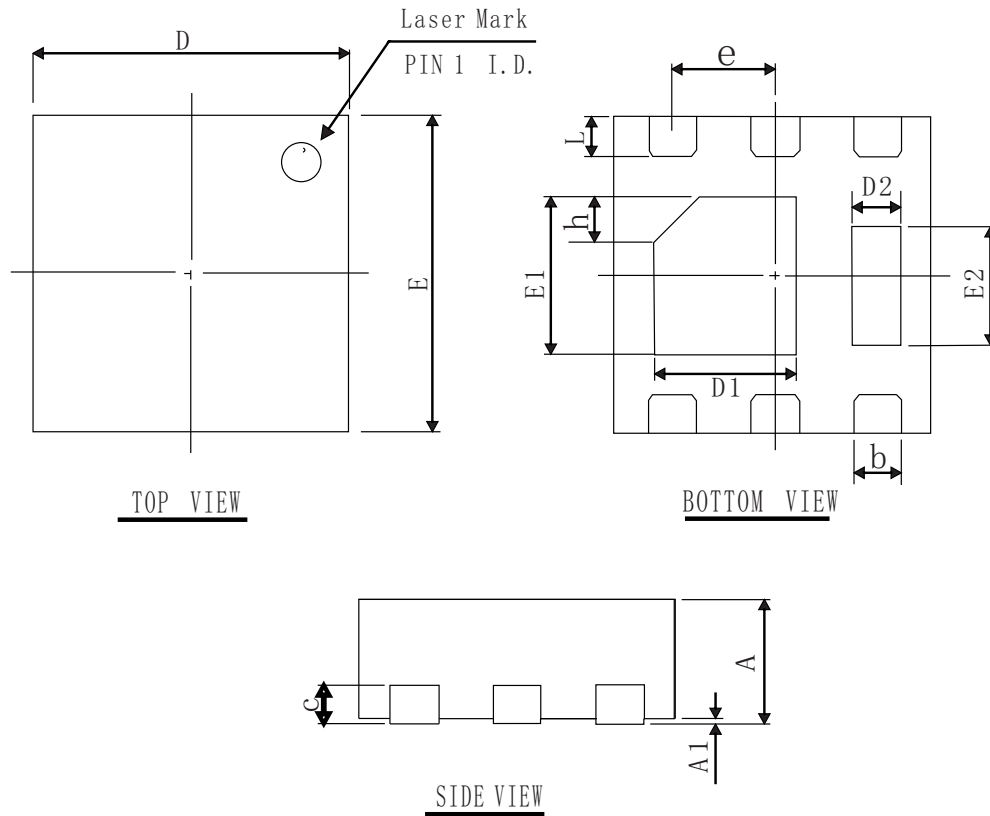


Source to Drain Voltage  
Body Diode Forward Characteristics

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**DFN 2X2 PACKAGE OUTLINE**



COMMON DIMENSIONS  
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.60	0.75	0.90
A1	0.00	0.02	0.10
b	0.15	0.25	0.40
D	1.80	2.00	2.25
E	1.80	2.00	2.25
D1	0.70	0.90	1.10
E1	0.75	1.00	1.20
D2	0.15	0.30	0.45
E2	0.45	0.75	0.95
L	0.15	0.25	0.40
h	0.15	0.25	0.40
c	0.203 REF		
e	0.65 BSC		

*Other thickness dimensions are as follows*

A	0.50	0.55	0.60
A	0.40	0.45	0.50

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